

RF AMPLIFIER

MODEL *TM9723*

Available as: TM9723, 4 Pin TO-8 (T4)
 TN9723, 4 Pin Surface Mount (SM3)
 FP9723, 4 Pin Flatpack (FP4)
 BX9723, Connectorized Housing (H1)
 PN9723, Reduced Size Surface Mount (SM11)

Features

- GaAs FET Amplifier; Medium Gain: 13 dB Typ.
- High Output Power: > +27 dBm Typical
- Operating Temp. - 55 °C to +85 °C
- Environmental Screening Available

Specifications

CHARACTERISTIC	TYPICAL Ta= 25 °C	MIN/MAX Ta = -55 °C to +85 °C
Frequency	10 - 1000 MHz	10 - 1000 MHz
Gain (dB)	13	12.0 Min.
Power @ 1 dB Comp. (dBm)	>+27	+26.0 Min.
Reverse Isolation (dB)	- 18	-17.0 Max.
VSWR In	<1.75:1	2.0:1 Max.
VSWR Out	<1.5:1	2.0:1 Max.
Noise figure (dB)	<4.0	8.0* Max.
Power Vdc	+15	+15
mA	185	195 Max.

Note: Care should always be taken to effectively ground the case of each unit.

Typical Intermodulation Performance at 25 ° C

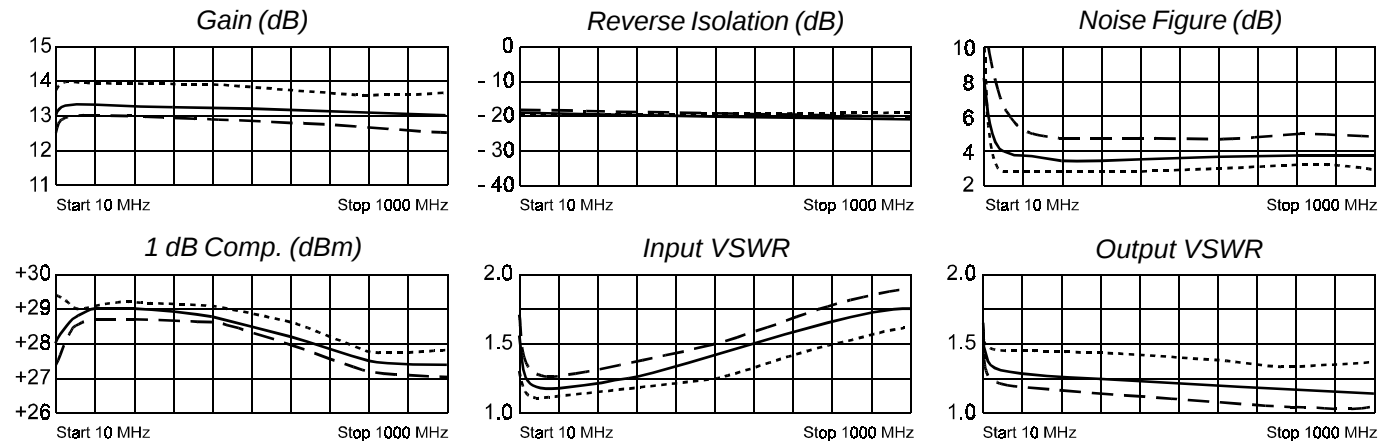
Second Order Harmonic Intercept Point +52 (Typ.)
 Second Order Two Tone Intercept Point +48 (Typ.)
 Third Order Two Tone Intercept Point +40 (Typ.)

Maximum Ratings

Ambient Operating Temperature -55°C to + 100 °C
 Storage Temperature -62°C to + 125 °C
 Case Temperature + 125 °C
 DC Voltage + 17Volts
 Continuous RF Input Power + 18 dBm
 Short Term RF Input Power 150 Milliwatts
 (1 Minute Max.)
 Maximum Peak Power 0.3 Watt
 (3 µsec Max.)

* Noise Figure is > 8.0 dB below 30 MHz

Typical Performance Data



Legend ——— + 25 °C - - - + 85 °C -55 °C

Linear S-Parameters

FREQ. MHz	S11		S21		S12		S22	
	Mag.	Deg.	Mag.	Deg.	Mag.	Deg.	Mag.	Deg.
10	.21	- 57	4.51	-161	.106	11	.20	139
50	.09	- 41	4.69	179	.108	0	.13	186
100	.08	- 42	4.69	172	.109	- 2	.12	164
200	.10	- 58	4.70	161	.110	- 8	.11	159
400	.13	- 80	4.65	140	.108	-17	.09	147
600	.19	-100	4.56	120	.104	-27	.08	135
800	.23	-121	4.48	101	.100	-35	.07	115
1000	.29	-139	4.47	83	.097	-34	.04	79

Amplifonix

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